Silicon NPN Power Transistors 2SC3300

DESCRIPTION

·With TO-3PN package
·Low saturation voltage
·Wide area of safe operation

APPLICATIONS

·Power and general purpose application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

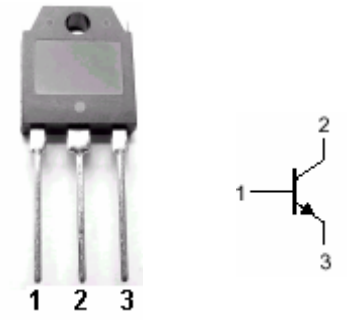


Fig.1 simplified outline (TO-3PN) and symbol

ABSOLUTE MAXIMUM RATINGS (TC=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		15	A
I_{CM}	Collector current-peak		25	A
P_C	Collector power dissipation	T_C=25□	100	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA ;I_B=0	100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ;I_E=0	100			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	6			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=10A ;I_B=1A			0.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=10A ;I_B=1A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=100V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=5A ; V_{CE}=4V	30		120	

PACKAGE OUTLINE

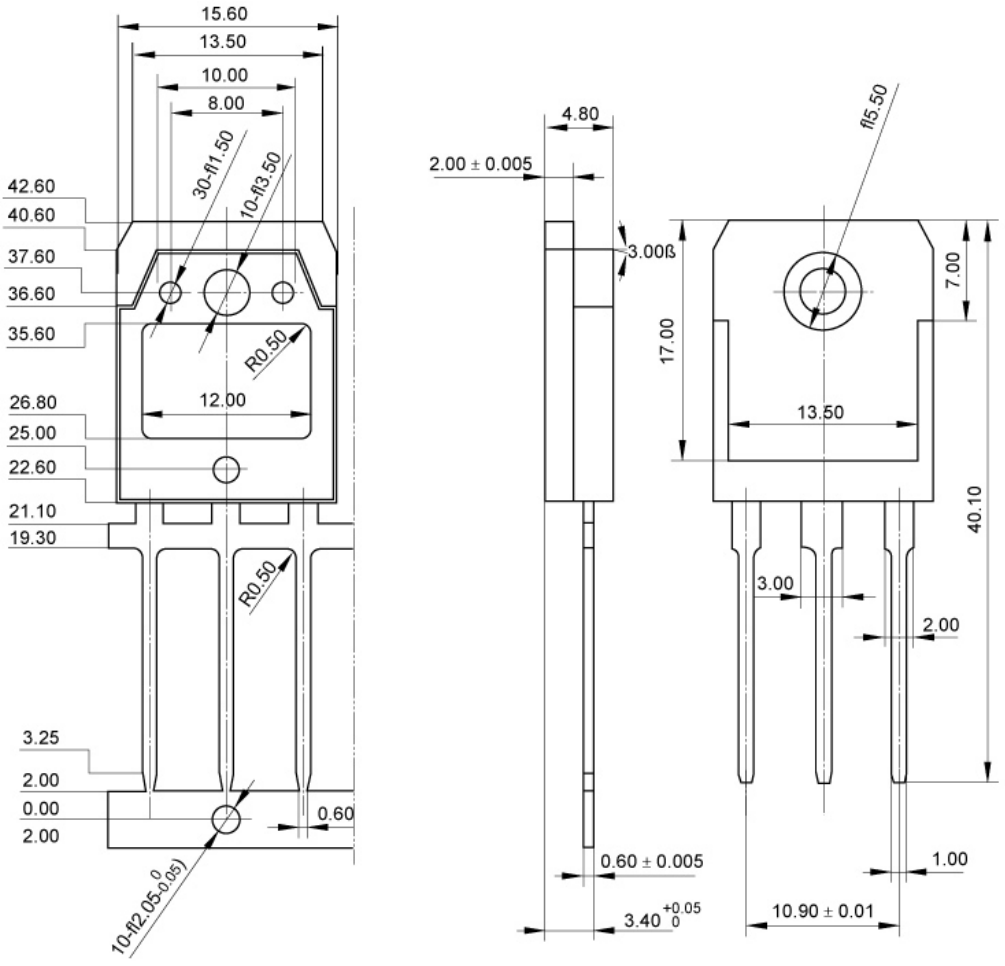


Fig.2 outline dimensions